

Appl. No. 09/841,582
Amdt. Dated June 30, 2008
Reply to Office Action of December 31, 2007

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AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-5. (Canceled)

6. (Currently Amended) A pseudo wafer structure comprising: a plurality of semiconductor chips each being a tested known good die and having at least their electrodes formed solely on one surface thereof, wherein the one surface at which the electrodes are formed is releasably adhered to an adhesive layer of material sheet that is secured to a substrate, wherein interspaces between each individual one of said chips and bottom surfaces opposite the electrodes thereof are continuously covered with said protective material, and the chips are bonded with each other via the protective material to thereby form the pseudo-wafer, there being substantially none of the protective material formed on the one surface at which the electrodes are formed, and further wherein the adhesive layer of material loses its adhesive characteristics upon application of a specified treatment ~~the electrodes being in contact with a solder material and further comprising a layer of silicon dioxide formed over the one surface at which the electrodes are formed upon removal of said adhesive sheet and a passivation layer formed over the silicon dioxide having openings at locations corresponding to the electrodes.~~

7. (Original) The pseudo wafer according to claim 6 wherein said protective material comprises either one of an organic insulating resin and an inorganic insulating material.

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8. (Previously Presented) The pseudo wafer according to claim 6 wherein said plurality of semiconductor chips arrayed thereon are diced at a position of said protective material between said plurality of semiconductor chips and thereafter mounted on a packaging substrate such that the protective material adjacent the side surfaces of the semiconductor chip is cut to provide substantially vertical side walls of protective material formed adjacent the sides of the semiconductor chip.

9. (Cancelled) The pseudo wafer according to claim 8 wherein a solder bump is formed on said electrode.

10. (Previously Presented) The pseudo wafer according to claim 6 wherein the adhesive properties of said adhesive sheet are released upon the application of ultra violet light.